

OK  
to  
file  
11/19/04

**AMENDMENTS TO THE CLAIMS**

1. (Previously Presented): A method of crystallizing amorphous silicon, comprising:  
depositing an inducing substance for silicon crystallization on an exposed surface of an amorphous silicon layer by plasma exposure; and  
annealing the amorphous silicon layer,  
wherein the annealing is carried out for less than about 50 minutes.
2. (Previously Presented): A method of crystallizing amorphous silicon, comprising:  
providing a substrate on which an amorphous silicon layer is formed;  
depositing an inducing substance for silicon crystallization on an exposed surface of an amorphous silicon layer by plasma exposure; and  
annealing the amorphous silicon layer,  
wherein the annealing is carried out for less than about 50 minutes.
3. (Original): The method of claim 2, wherein the substrate is prepared by forming the amorphous silicon layer on an isolated substrate.
4. (Original): The method of claim 3, wherein a buffer layer is formed between the isolated substrate and the amorphous silicon layer.
5. (Original): The method of claim 2, the method further comprising the step of forming a second amorphous silicon layer after the plasma exposure.
6. (Original): The method of claim 2, the method further comprising the step of selectively forming an insulating layer on the substrate before the step of depositing an inducing substance for silicon crystallization.
7. (Original): The method of claim 1, wherein the plasma is RF plasma.
8. (Original): The method of claim 1, wherein the plasma is a DC plasma.
9. (Original): The method of claim 1, wherein the plasma is microwave plasma.